

$V_{DSS}$	1200V
$R_{DS(on)}$ (Typ.)	80mΩ
$I_D$	40A

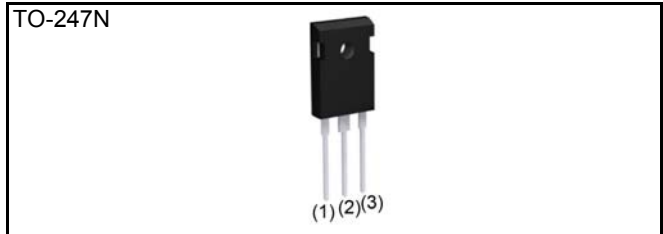
### ●Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant
- 7) Qualified to AEC-Q101

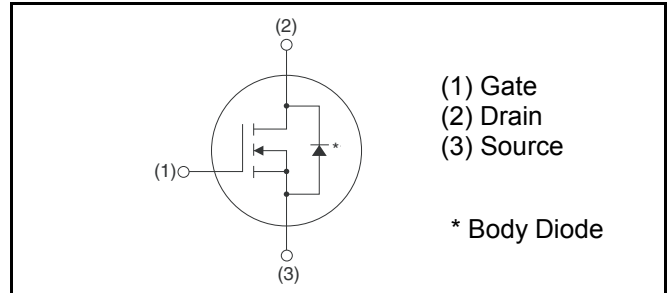
### ●Application

- Automobile
- Switch mode power supplies

### ●Outline



### ●Inner circuit



### ●Packaging specifications

Package	TO-247N	
Type	Packing	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	30
	Packing code	C11
	Marking	SCT2080KE

### ●Absolute maximum ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit	
Drain - Source voltage	$V_{DSS}$	1200	V	
Continuous drain current	$T_c = 25^\circ\text{C}$	$I_D^{*1}$	40	A
	$T_c = 100^\circ\text{C}$	$I_D^{*1}$	28	A
Pulsed drain current	$I_{D,pulse}^{*2}$	80	A	
Gate - Source voltage (DC)	$V_{GSS}$	-6 to +22	V	
Gate - Source surge voltage ( $t_{surge} < 300\text{nsec}$ )	$V_{GSS\_surge}^{*3}$	-10 to +26	V	
Junction temperature	$T_j$	175	$^\circ\text{C}$	
Range of storage temperature	$T_{stg}$	-55 to +175	$^\circ\text{C}$	

●Electrical characteristics (T<sub>a</sub> = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA	1200	-	-	V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 1200V, V <sub>GS</sub> = 0V T <sub>j</sub> = 25°C	-	1	10	μA
			-	2	-	
Gate - Source leakage current	I <sub>GSS+</sub>	V <sub>GS</sub> = +22V, V <sub>DS</sub> = 0V	-	-	100	nA
Gate - Source leakage current	I <sub>GSS-</sub>	V <sub>GS</sub> = -6V, V <sub>DS</sub> = 0V	-	-	-100	nA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 4.4mA	1.6	2.8	4.0	Ω

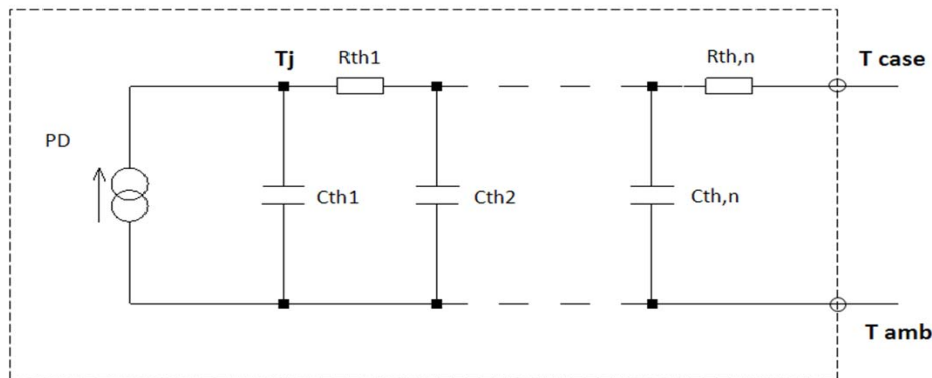
●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R <sub>thJC</sub>	-	0.44	0.57	°C/W

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R <sub>th1</sub>	7.80E-02	K/W
R <sub>th2</sub>	1.97E-01	
R <sub>th3</sub>	1.62E-01	

Symbol	Value	Unit
C <sub>th1</sub>	5.00E-03	Ws/K
C <sub>th2</sub>	1.80E-02	
C <sub>th3</sub>	2.49E-01	



●Electrical characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Static drain - source on - state resistance	$R_{DS(on)}^{*4}$	$V_{GS} = 18\text{V}, I_D = 10\text{A}$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	-	80 125	117 -	m $\Omega$
Gate input resistance	$R_G$	$f = 1\text{MHz}$ , open drain	-	6.3	-	$\Omega$
Transconductance	$g_{fs}^{*4}$	$V_{DS} = 10\text{V}, I_D = 10\text{A}$	-	3.7	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$	-	2080	-	pF
Output capacitance	$C_{oss}$	$V_{DS} = 800\text{V}$	-	77	-	
Reverse transfer capacitance	$C_{rss}$	$f = 1\text{MHz}$	-	16	-	
Effective output capacitance, energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ $V_{DS} = 0\text{V to } 500\text{V}$	-	116	-	pF
Turn - on delay time	$t_{d(on)}^{*4}$	$V_{DD} = 400\text{V}, V_{GS} = 18\text{V}$	-	35	-	ns
Rise time	$t_r^{*4}$	$I_D = 10\text{A}$	-	36	-	
Turn - off delay time	$t_{d(off)}^{*4}$	$R_L = 40\Omega$	-	76	-	
Fall time	$t_f^{*4}$	$R_G = 0\Omega$	-	22	-	
Turn - on switching loss	$E_{on}^{*4}$	$V_{DD} = 600\text{V}, I_D = 10\text{A}$ $V_{GS} = 18\text{V}/0\text{V}$ $R_G = 0\Omega, L = 500\mu\text{H}$	-	174	-	$\mu\text{J}$
Turn - off switching loss	$E_{off}^{*4}$	* $E_{on}$ includes diode reverse recovery	-	51	-	

●Gate Charge characteristics ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	$Q_g^{*4}$	$V_{DD} = 400\text{V}$	-	106	-	nC
Gate - Source charge	$Q_{gs}^{*4}$	$I_D = 10\text{A}$	-	27	-	
Gate - Drain charge	$Q_{gd}^{*4}$	$V_{GS} = 18\text{V}$	-	31	-	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 400\text{V}, I_D = 10\text{A}$	-	9.7	-	V

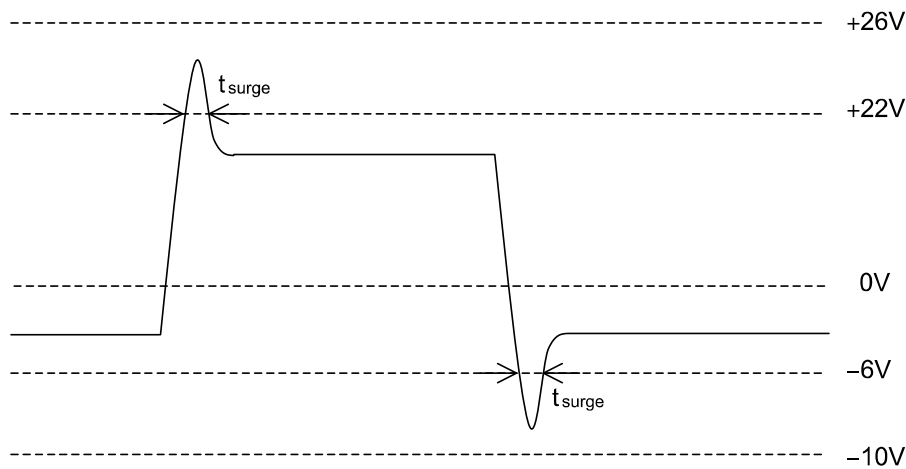
●Body diode electrical characteristics (Source-Drain) ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Body diode continuous, forward current	$I_S^{*1}$	$T_c = 25^\circ\text{C}$	-	-	40	A
Body diode direct current, pulsed	$I_{SM}^{*2}$		-	-	80	A
Forward voltage	$V_{SD}^{*4}$	$V_{GS} = 0\text{V}, I_S = 10\text{A}$	-	4.6	-	V
Reverse recovery time	$t_{rr}^{*4}$	$I_F = 10\text{A}, V_R = 400\text{V}$ $di/dt = 150\text{A}/\mu\text{s}$	-	31	-	ns
Reverse recovery charge	$Q_{rr}^{*4}$		-	44	-	nC
Peak reverse recovery current	$I_{rrm}^{*4}$		-	2.3	-	A

\*1 Limited only by maximum temperature allowed.

\*2  $PW \leq 10\mu\text{s}$ , Duty cycle  $\leq 1\%$

\*3 Example of acceptable  $V_{GS}$  waveform



\*4 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

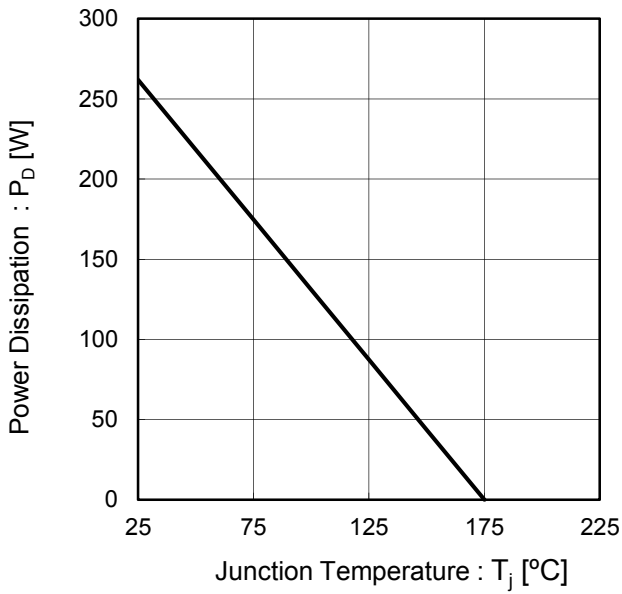


Fig.2 Maximum Safe Operating Area

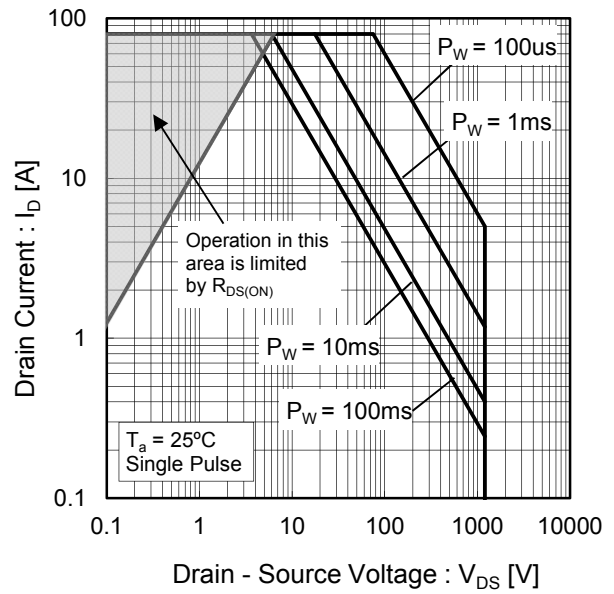
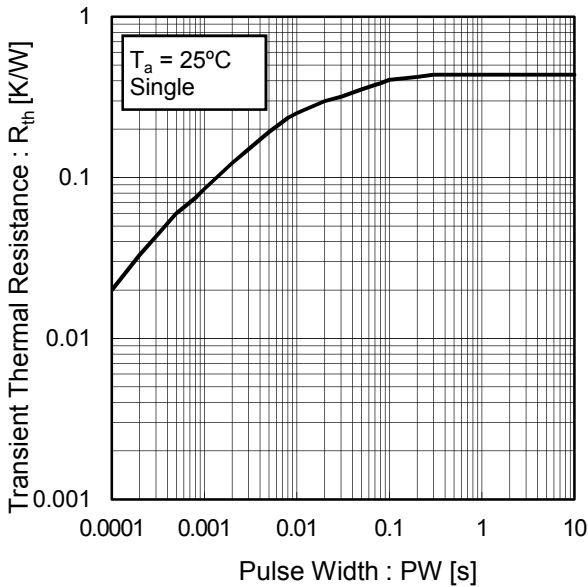


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

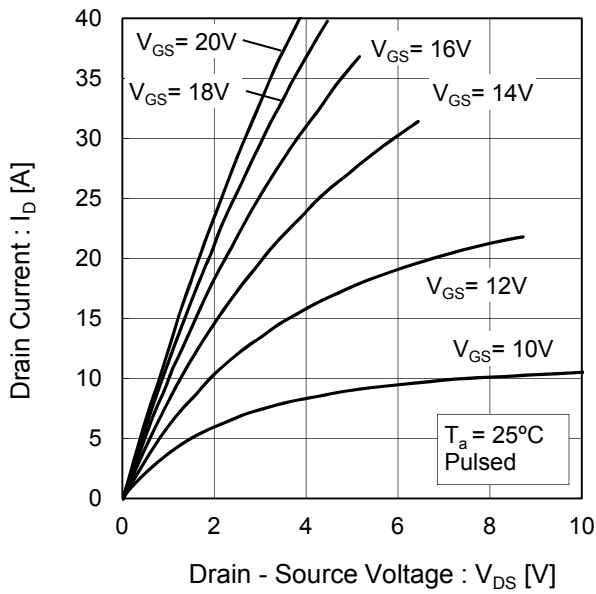


Fig.5 Typical Output Characteristics(II)

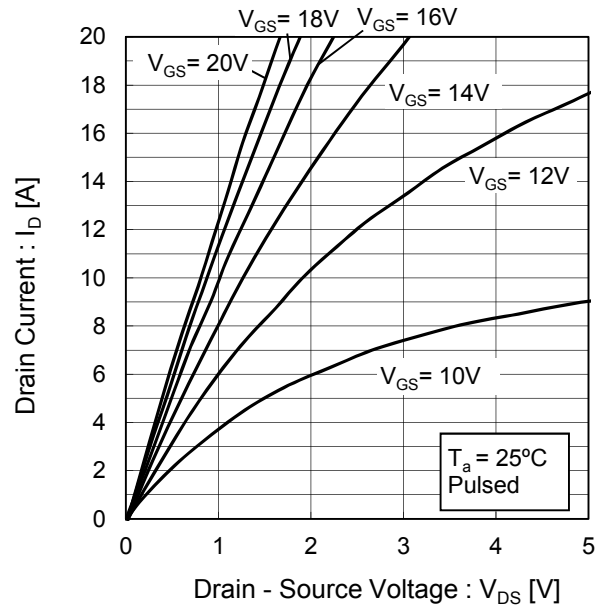


Fig.6 Typical Output Characteristics(I)

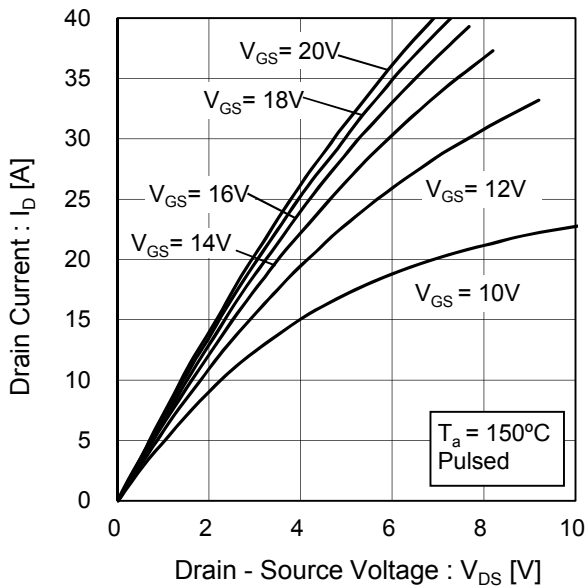
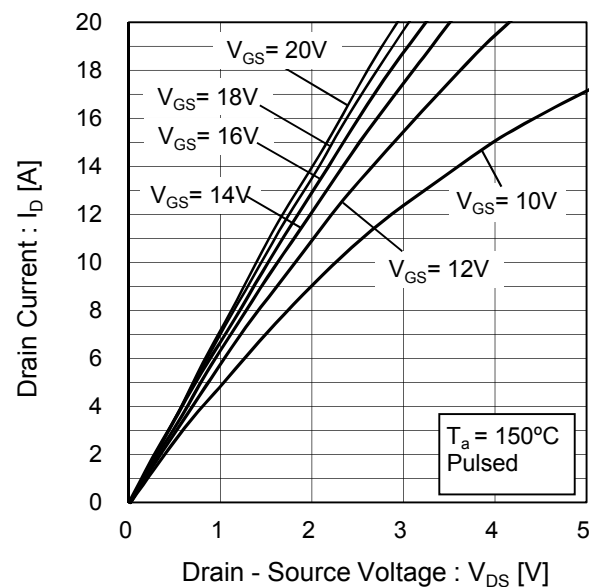


Fig.7 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics

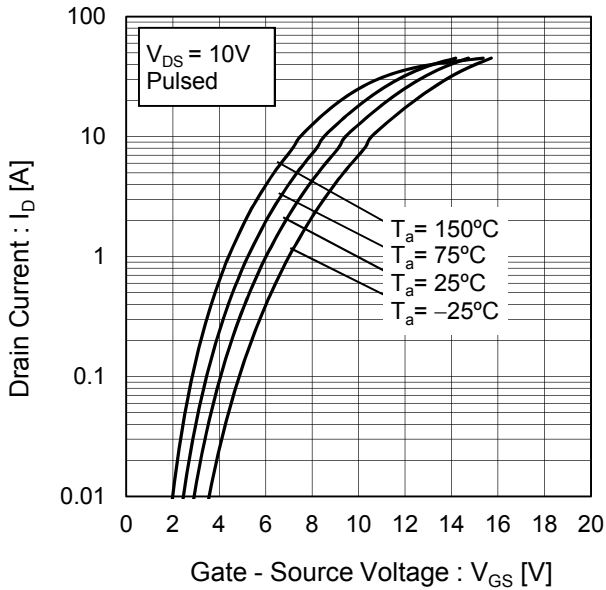


Fig.9 Typical Transfer Characteristics (II)

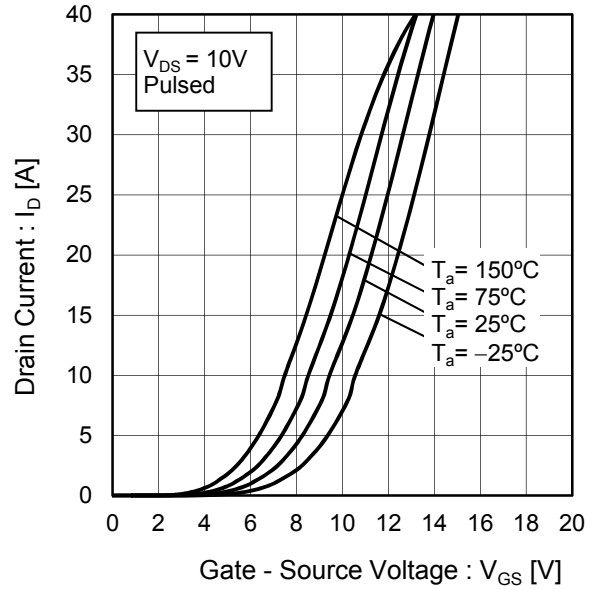


Fig.10 Gate Threshold Voltage vs. Junction Temperature

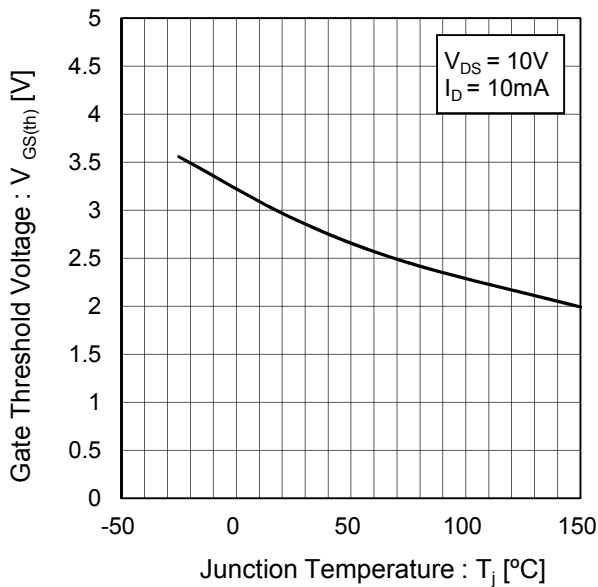
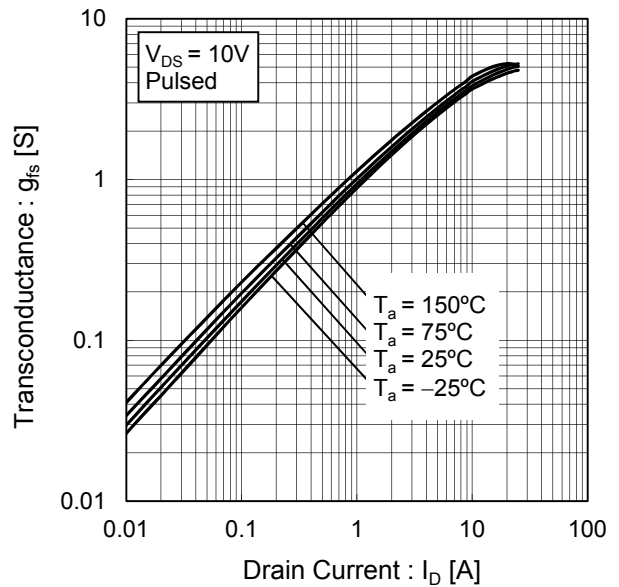


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate - Source Voltage

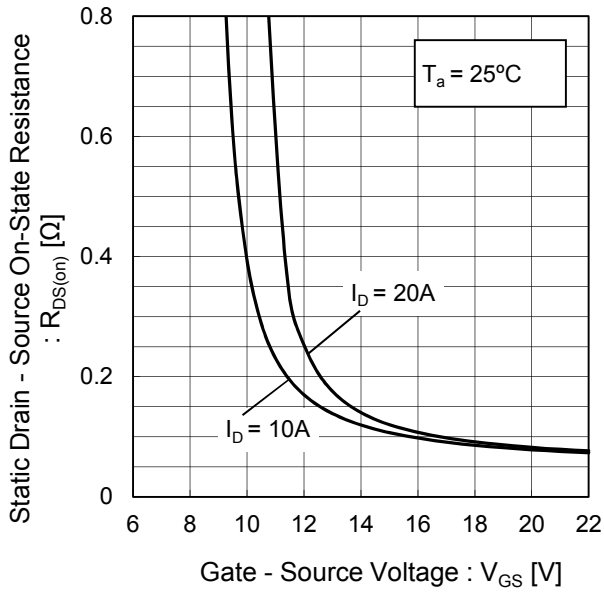


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

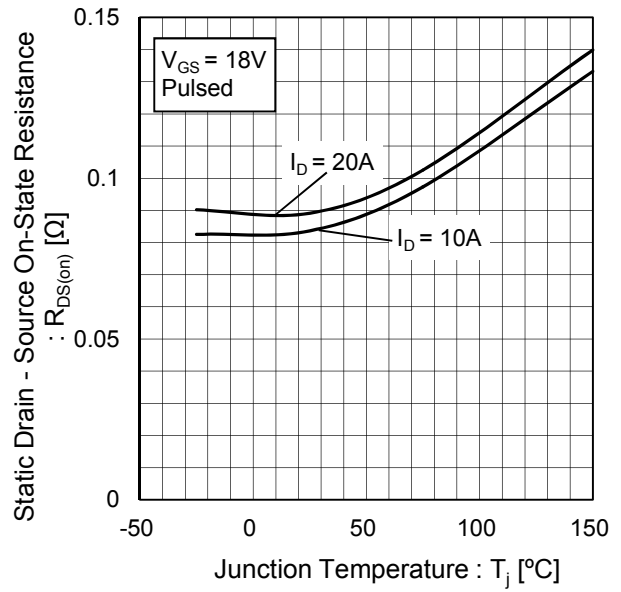
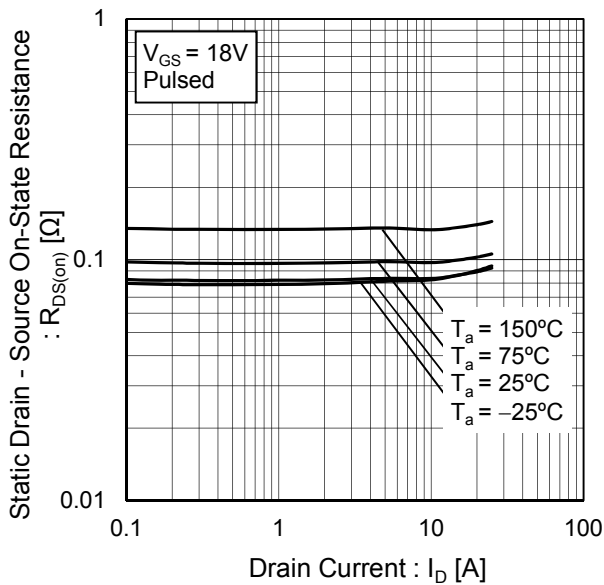


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current





●Electrical characteristic curves

Fig.15 Typical Capacitance vs. Drain - Source Voltage

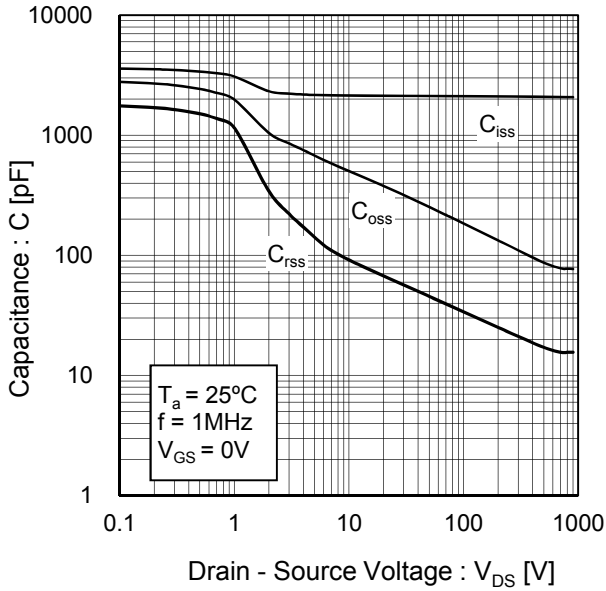


Fig.16 C<sub>oss</sub> Stored Energy

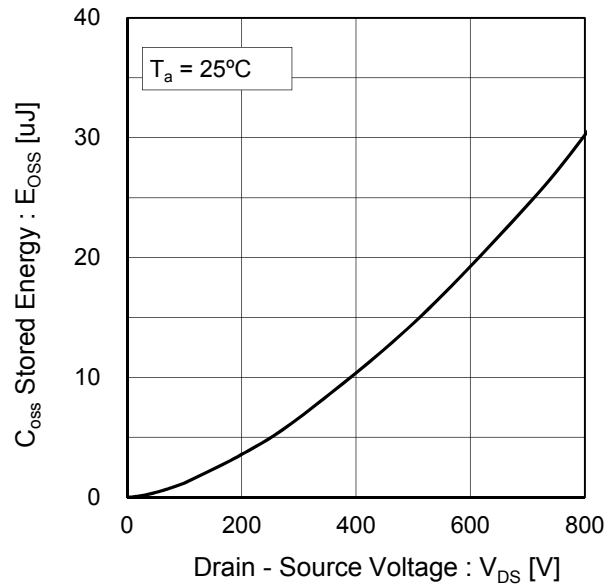


Fig.17 Switching Characteristics

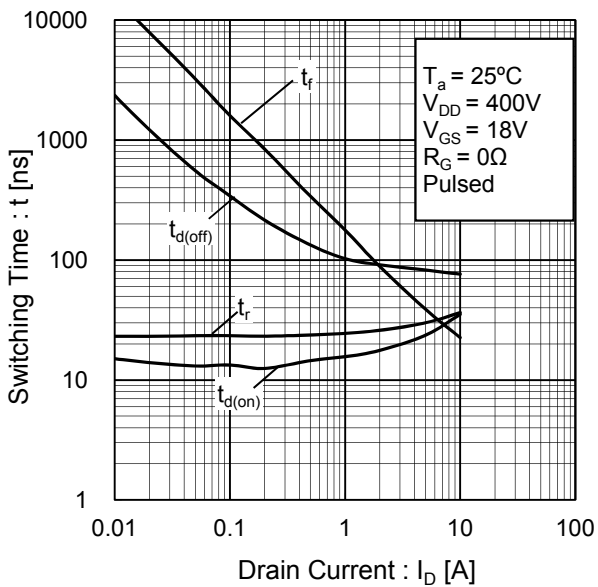
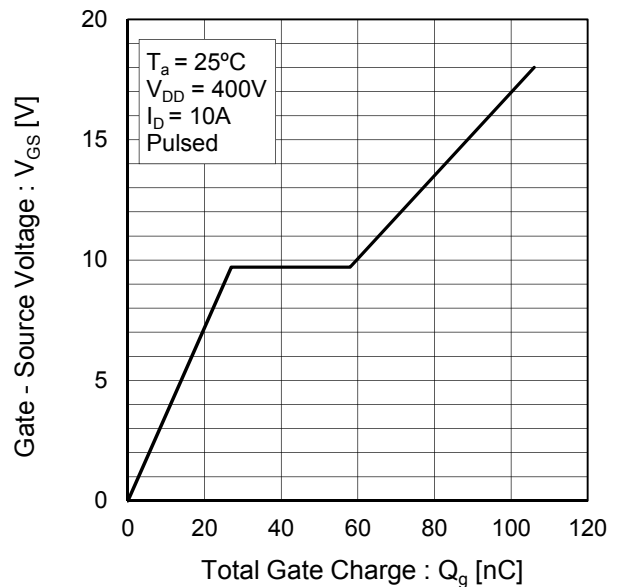


Fig.18 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

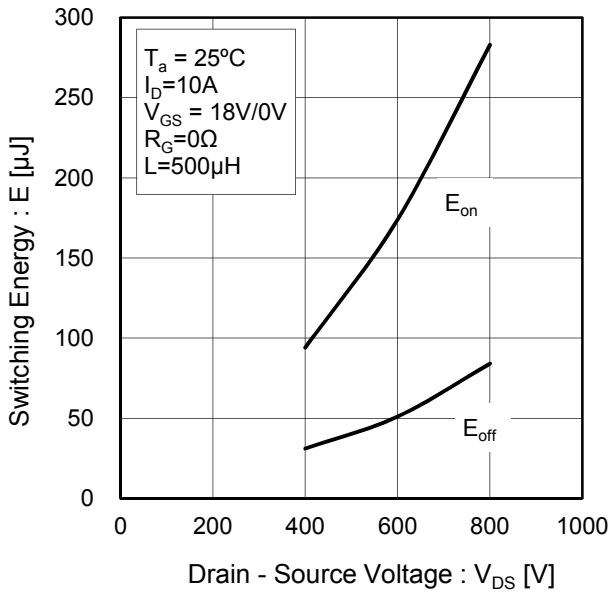


Fig.20 Typical Switching Loss vs. Drain Current

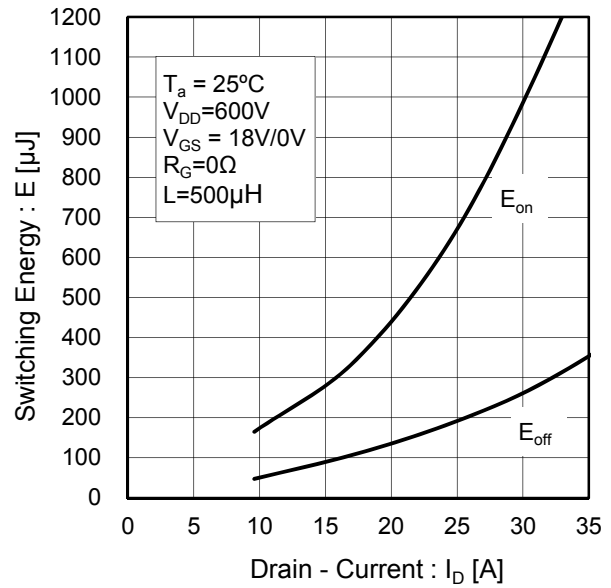
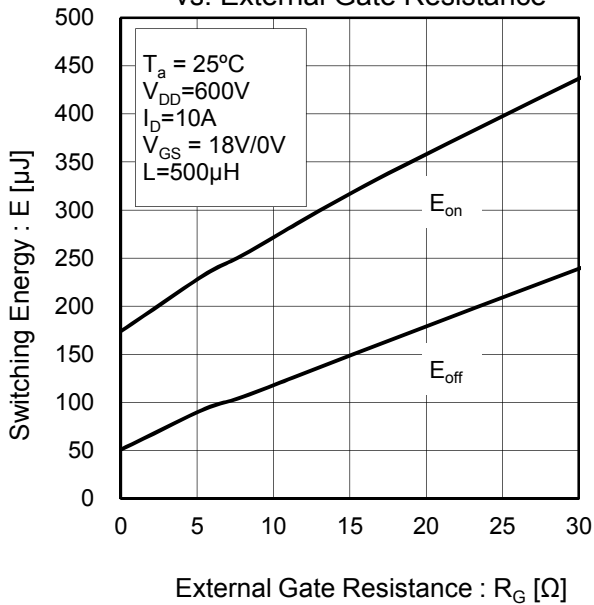


Fig.21 Typical Switching Loss vs. External Gate Resistance



●Electrical characteristic curves

Fig.22 Body Diode Forward Current vs. Source - Drain Voltage

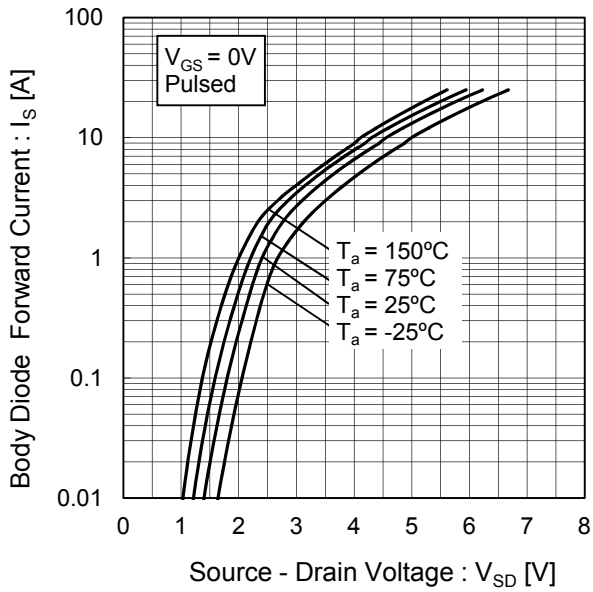
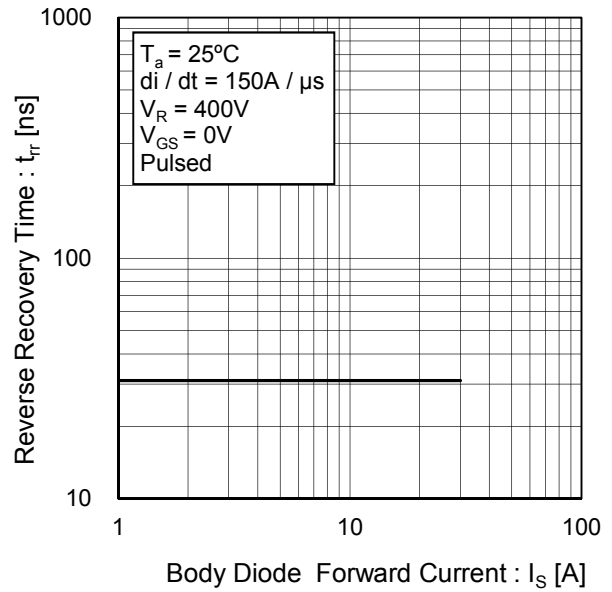


Fig.23 Reverse Recovery Time vs. Body Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

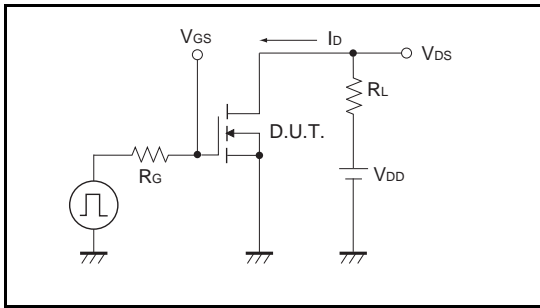


Fig.1-2 Switching Waveforms

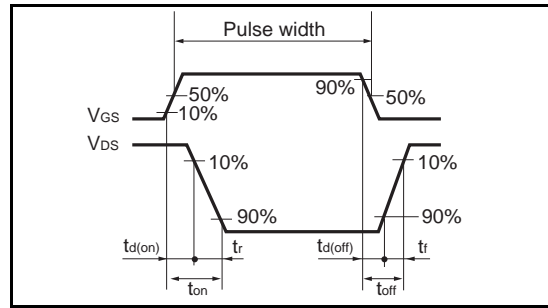


Fig.2-1 Gate Charge Measurement Circuit

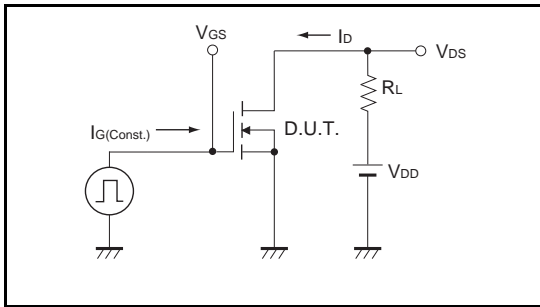


Fig.2-2 Gate Charge Waveform

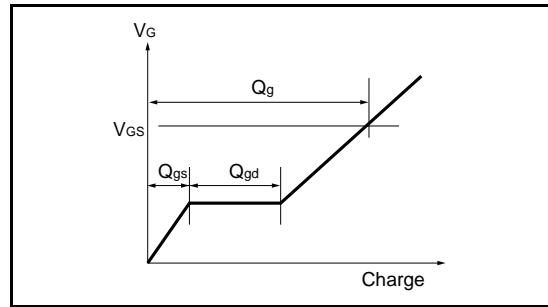


Fig.3-1 Switching Energy Measurement Circuit

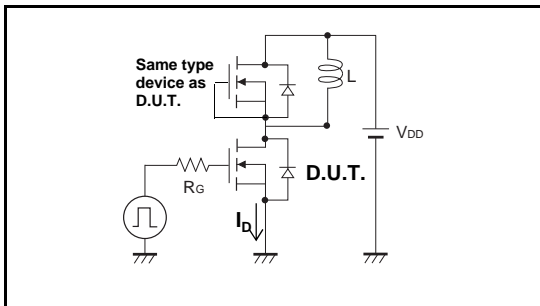


Fig.3-2 Switching Waveforms

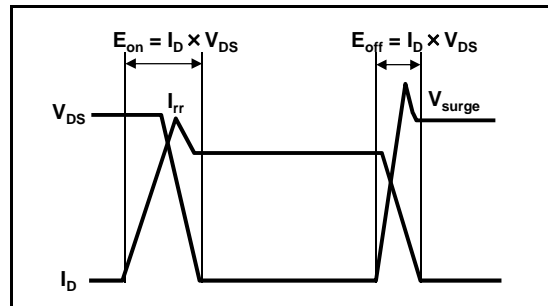


Fig.4-1 Reverse Recovery Time Measurement Circuit

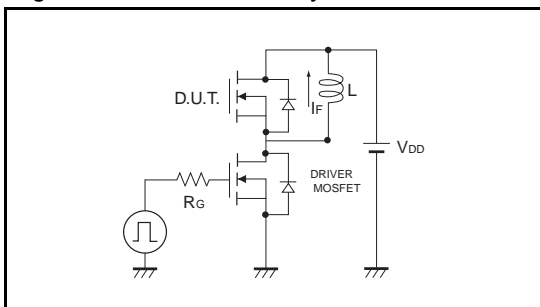
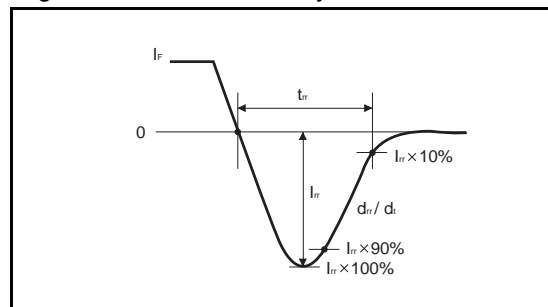


Fig.4-2 Reverse Recovery Waveform



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